

DATA SHEET

PTB32001X; PTB32003X; PTB32005X NPN microwave power transistors

Product specification
Supersedes data of November 1994

1997 Feb 18

NPN microwave power transistors

PTB32001X; PTB32003X;
PTB32005X

FEATURES

- Diffused emitter ballasting resistors providing excellent current sharing and withstanding a high VSWR
- Interdigitated structure provides high emitter efficiency
- Multicell geometry gives good balance of dissipated power and low thermal resistance
- Localized thick oxide auto-alignment process and gold sandwich metallization ensure an optimum temperature profile and excellent performance and reliability.

APPLICATIONS

Common-base, class B power amplifiers up to 4.2 GHz.

DESCRIPTION

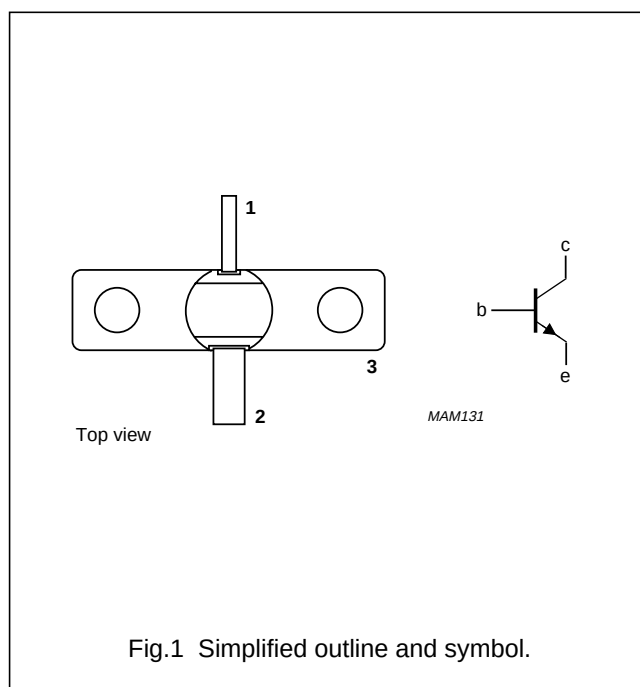
NPN silicon planar epitaxial microwave power transistor in a metal ceramic SOT440A flange package with base connected to the flange.

MARKING

TYPE NUMBER	MARKING CODE
PTB32001X	3201X
PTB32003X	3203X
PTB32005X	3205X

PINNING - SOT440A

PIN	DESCRIPTION
1	collector
2	emitter
3	base connected to flange



QUICK REFERENCE DATA

Microwave performance up to $T_{mb} = 25\text{ }^{\circ}\text{C}$ in a common-base class B circuit.

TYPE NUMBER	MODE OF OPERATION	f (GHz)	V _{CC} (V)	P _L (W)	G _{po} (dB)	η _c (%)	Z _i (Ω)	Z _L (Ω)
PTB32001X	CW	3	24	≥1.3	≥8	≥35	15 + j31	5.5 + j10
PTB32003X	CW	3	24	≥2.5	≥8	≥35	5.5 + j29	5 – j2.2
PTB32005X	CW	3	24	≥4.5	≥8	≥35	2.8 + j20	4 – j7

WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO slab is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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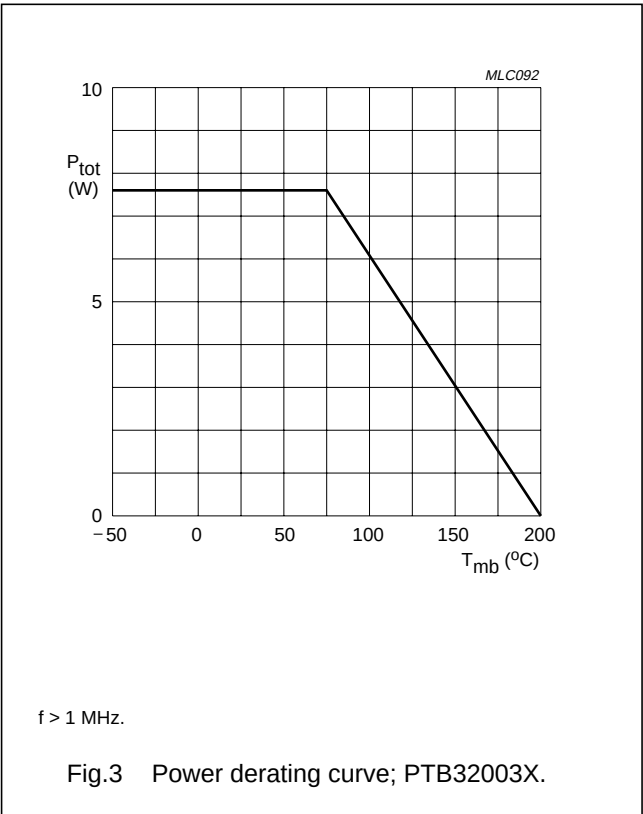
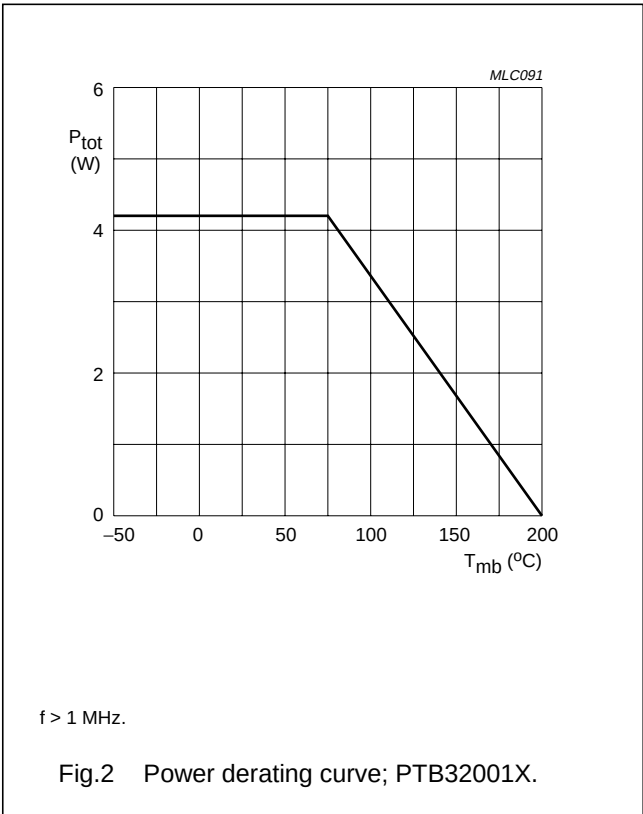
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	40	V
V _{CEO}	collector-emitter voltage	open base	–	15	V
V _{CES}	collector-emitter voltage	R _{BE} = 0 Ω	–	40	V
V _{EBO}	emitter-base voltage	open collector	–	3.0	V
I _C	collector current (DC) PTB32001X PTB32003X PTB32005X		– – –	0.25 0.5 0.75	A A A
P _{tot}	total power dissipation PTB32001X PTB32003X PTB32005X	T _{mb} ≤ 75 °C; f > 1 MHz	– – –	4.2 7.6 8.7	W W W
T _{stg}	storage temperature range		–65	+200	°C
T _j	operating junction temperature		–	200	°C
T _{slid}	soldering temperature	t ≤ 10 s; note 1	–	235	°C

Note

1. Up to 0.3 mm from ceramic.



NPN microwave power transistors

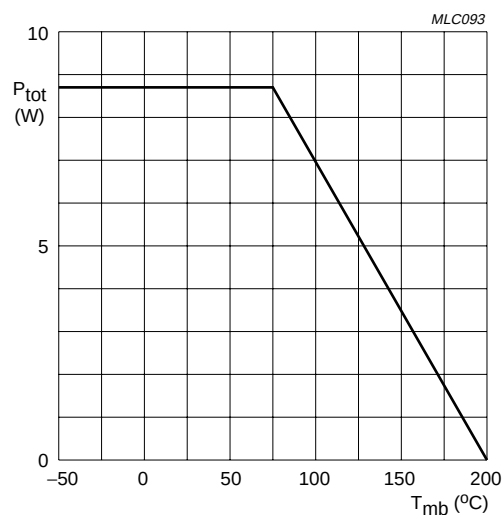
PTB32001X; PTB32003X;
PTB32005X $f > 1$ MHz.

Fig. 4 Power derating curve; PTB32005X.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_j = 75\ ^\circ\text{C}$		
	PTB32001X		22	K/W
	PTB32003X		12	K/W
	PTB32005X		10.5	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink	$T_j = 75\ ^\circ\text{C}$; note 1	0.7	K/W

Note

- See "Mounting recommendations in the General part of handbook SC19a".

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PTB32005X

CHARACTERISTICS

 $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage					
	PTB32001X	$I_C = 1\text{ mA}; I_E = 0$	40	—	—	V
	PTB32003X	$I_C = 2\text{ mA}; I_E = 0$	40	—	—	V
	PTB32005X	$I_C = 3\text{ mA}; I_E = 0$	40	—	—	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = 10\text{ mA}; R_{BE} = 0\text{ }\Omega$	40	—	—	V
I_{CBO}	collector cut-off current					
	PTB32001X	$V_{CE} = 24\text{ V}; I_E = 0$	—	—	10	μA
	PTB32003X	$V_{CE} = 24\text{ V}; I_E = 0$	—	—	20	μA
	PTB32005X	$V_{CE} = 24\text{ V}; I_E = 0$	—	—	30	μA
I_{EBO}	emitter cut-off current					
	PTB32001X	$V_{EB} = 1.5\text{ V}; I_C = 0$	—	—	0.2	μA
	PTB32003X	$V_{EB} = 1.5\text{ V}; I_C = 0$	—	—	0.4	μA
	PTB32005X	$V_{EB} = 1.5\text{ V}; I_C = 0$	—	—	0.6	μA
C_{cb}	collector-base capacitance					
	PTB32001X	$I_E = I_C = 0; V_{CB} = 24\text{ V}; V_{EB} = 1.5\text{ V}; f = 1\text{ MHz}$	—	2.2	—	pF
	PTB32003X	$I_E = I_C = 0; V_{CB} = 24\text{ V}; V_{EB} = 1.5\text{ V}; f = 1\text{ MHz}$	—	3	—	pF
	PTB32005X	$I_E = I_C = 0; V_{CB} = 24\text{ V}; V_{EB} = 1.5\text{ V}; f = 1\text{ MHz}$	—	3.8	—	pF
C_{ce}	collector-emitter capacitance					
	PTB32001X	$I_E = I_C = 0; V_{CB} = 24\text{ V}; V_{EB} = 1.5\text{ V}; f = 1\text{ MHz}$	—	0.3	—	pF
	PTB32003X	$I_E = I_C = 0; V_{CB} = 24\text{ V}; V_{EB} = 1.5\text{ V}; f = 1\text{ MHz}$	—	0.6	—	pF
	PTB32005X	$I_E = I_C = 0; V_{CB} = 24\text{ V}; V_{EB} = 1.5\text{ V}; f = 1\text{ MHz}$	—	0.9	—	pF

APPLICATION INFORMATION

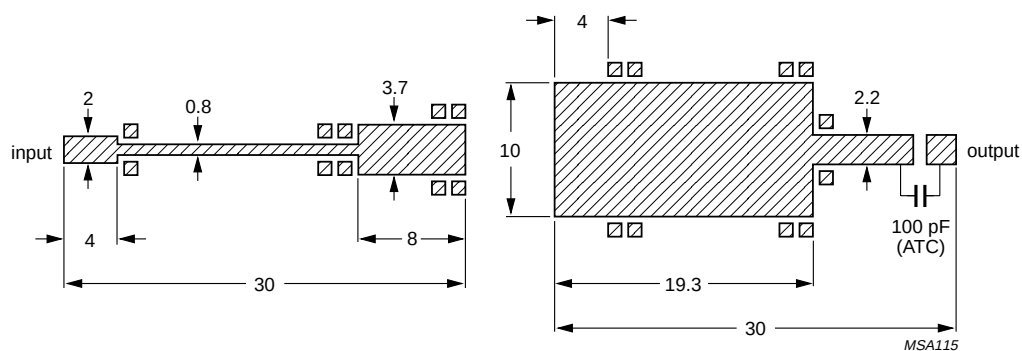
Microwave performance in a common-base class B selective amplifier circuit; see note 1.

MODE OF OPERATION	TYPE NUMBER	f (GHz)	V_{CC} (V)	P_L (W)	G_{po} (dB)	η_c (%)
Class B (CW)	PTB32001X	3	24	>1.3; typ. 1.8	>8; typ. 9.5	>35; typ. 45
	PTB32003X	3	24	>2.5; typ. 3.0	>8; typ. 9.5	>35; typ. 45
	PTB32005X	3	24	>4.5; typ. 5.5	>8; typ. 9.5	>35; typ. 45

Note

1. Circuit consists of prematching circuit board in combination with complementary input and output slug tuners.

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PTB32005X

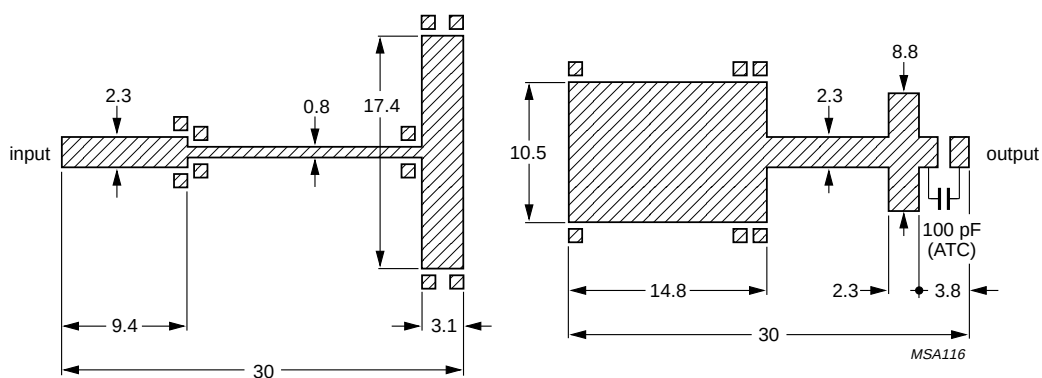
Dimensions in mm.

Thickness: 0.8 mm.

Permittivity: $\epsilon_r = 2.55$.

Substrate: circuits on a double copper-clad printed circuit board Teflon fibre glass dielectric.

Fig.5 Prematching test circuit board for PTB32001X.



Dimensions in mm.

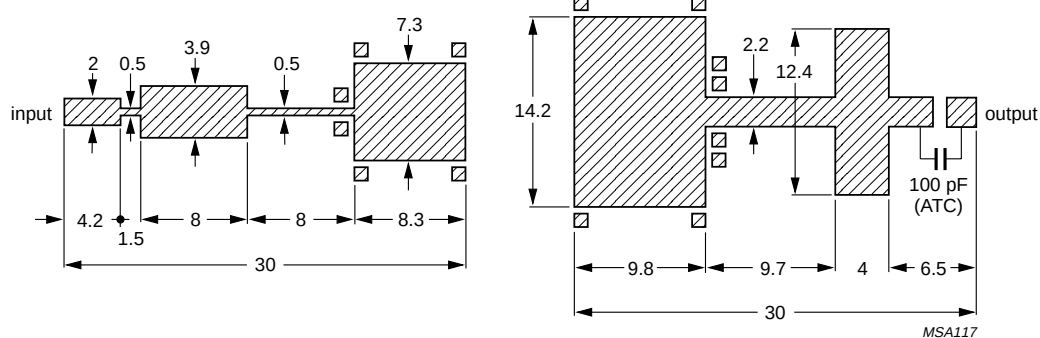
Thickness: 0.8 mm.

Permittivity: $\epsilon_r = 2.55$.

Substrate: circuits on a double copper-clad printed circuit board Teflon fibre glass dielectric.

Fig.6 Prematching test circuit board for PTB32003X.

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PTB32005X

Dimensions in mm.

Thickness: 0.8 mm.

Permittivity: $\epsilon_r = 2.55$.

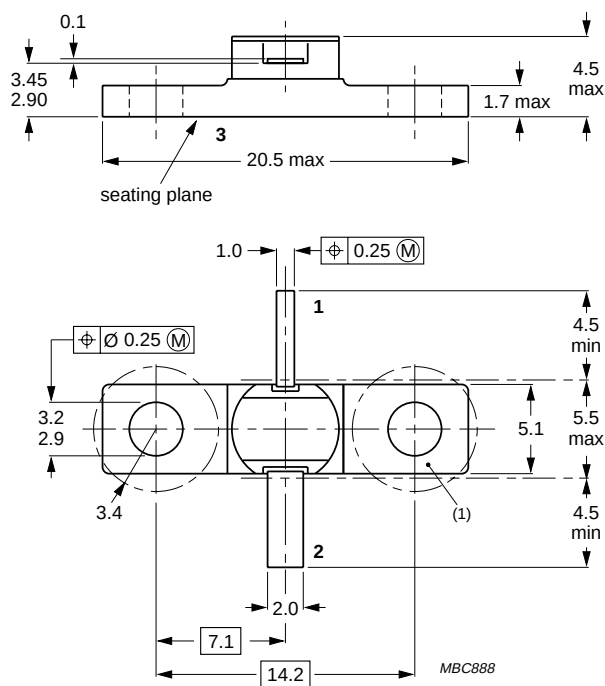
Substrate: circuits on a double copper-clad printed board Teflon fibreglass dielectric.

Fig.7 Prematching test circuit board for PTB32005X.

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PACKAGE OUTLINE



(1) Flatness of this area ensures full thermal contact with bolt head.

Dimensions in mm.

Torque on screws: max. 0.5 Nm.

Recommended screw: M2.5.

Fig.8 SOT440A.

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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NOTES

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NOTES

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